Product data sheet

1. General description

NPN low V_{CEsat} transistor in a medium power SOT89 (SC-62) package.

PNP complement: PBSS5540X.

2. Features and benefits

- High h_{FE} and low V_{CEsat} at high current operation
- High collector current capability: I_C maximum 4 A
- High efficiency leading to less heat generation.
- AEC-Q101 qualified

3. Applications

- Medium power peripheral drivers (e.g. fan and motor)
- Strobe flash units for DSC and mobile phones
- Inverter applications (e.g. TFT displays)
- · Power switch for LAN and ADSL systems
- Medium power DC-to-DC conversionc
- · Battery chargers.

4. Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|--------------------|---|--|-----|-----|-----|------|
| V _{CEO} | collector-emitter voltage | open base | - | - | 40 | V |
| Ic | collector current | | - | - | 4 | Α |
| I _{CM} | peak collector current | single pulse; t _p ≤ 10 ms | - | - | 10 | Α |
| R _{CEsat} | collector-emitter saturation resistance | I_C = 5 A; I_B = 500 mA; $t_p \le 300$ μs; pulsed; δ ≤ 0.02; T_{amb} = 25 °C | - | 40 | 71 | mΩ |



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5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-------------|--------------------|----------------|
| 1 | Е | emitter | | С |
| 2 | С | collector | | |
| 3 | В | base | | B — (|
| | | | 3 2 1 | Ė |
| | | | SOT89 | sym123 |

6. Ordering information

Table 3. Ordering information

| Type number | Package | | | | | |
|-------------|---------|--|---------|--|--|--|
| | Name | Description | Version | | | |
| PBSS4540X | SOT89 | plastic, surface-mounted package; 3 leads; 1.5 mm pitch; 4.5 mm x 2.5 mm x 1.5 mm body | SOT89 | | | |

7. Marking

Table 4. Marking codes

| Type number | Marking code[1] |
|-------------|-----------------|
| PBSS4540X | %1B |

[1] % = placeholder for manufacturing site code

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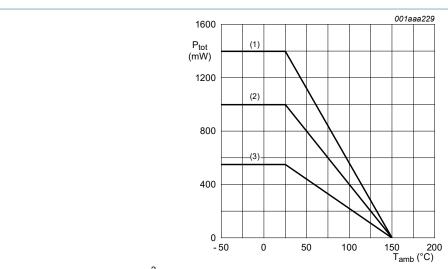
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | | Min | Max | Unit |
|------------------|-----------------------------------|--|---------|-----|------|------|
| V _{CBO} | collector-base voltage | open emitter | | - | 40 | V |
| V _{CEO} | collector-emitter voltage | open base | | - | 40 | V |
| V _{EBO} | emitter-base voltage | open collector | | - | 6 | V |
| I _C | collector current | | | - | 4 | Α |
| I _{CRM} | repetitive peak collector current | $\delta \le 0.02; t_p \le 10 \text{ ms}$ | [1] | - | 5 | А |
| I _{CM} | peak collector current | single pulse; t _p ≤ 10 ms | | - | 10 | Α |
| I _B | base current | | | - | 1 | Α |
| I _{BM} | peak base current | single pulse; t _p ≤ 1 ms | | - | 2 | Α |
| P _{tot} | total power dissipation | T _{amb} ≤ 25 °C | [1] [2] | - | 2.5 | W |
| | | | [1] | - | 0.55 | W |
| | | | [3] | - | 1 | W |
| | | | [4] | - | 1.4 | W |
| | | | [5] | - | 1.6 | W |
| T _j | junction temperature | | | - | 150 | °C |
| T _{amb} | ambient temperature | | | -65 | 150 | °C |
| T _{stg} | storage temperature | | | -65 | 150 | °C |

- Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] [3] Operated under pulsed conditions; $t_p \le 10$ ms; $\delta \le 0.2$.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm²
- [4] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².
- Device mounted on a 7 cm² ceramic PCB, 1 cm² single-sided copper and tin-plated. [5]



- (1) FR4 PCB; 6 cm² mounting pad for collector (2) FR4 PCB; 1 cm² mounting pad for collector
- (3) FR4; standard footprint

Power derating curves Fig. 1.

40 V, 5 A NPN low VCEsat (BISS) transistor

9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|----------------------|--|------------|---------|-----|-----|-----|------|
| R _{th(j-a)} | thermal resistance from junction to ambient | | [1] [2] | - | - | 50 | K/W |
| | | | [1] | - | - | 225 | K/W |
| | | | [3] | - | - | 125 | K/W |
| | | | [4] | - | - | 90 | K/W |
| | | | [5] | - | - | 80 | K/W |
| $R_{th(j-sp)}$ | thermal resistance from junction to solder point | | | - | - | 16 | K/W |

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Operated under pulsed conditions; $t_p \le 10$ ms; $\delta \le 0.2$.
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².
- [4] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².
- [5] Device mounted on a 7 cm² ceramic PCB, 1 cm² single-sided copper and tin-plated.

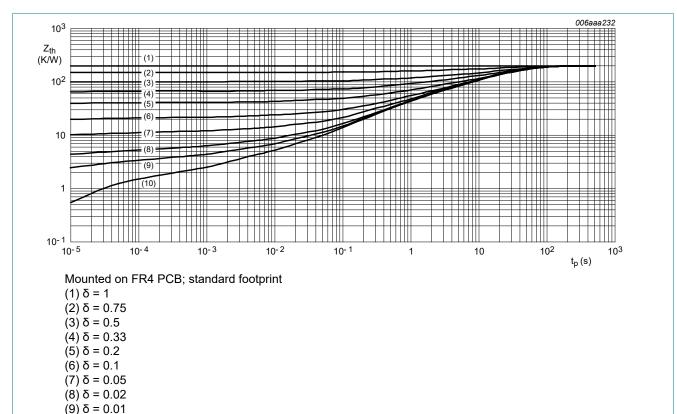


Fig. 2. Transient thermal impedance as a function of pulse duration; typical values

 $(10) \delta = 0$

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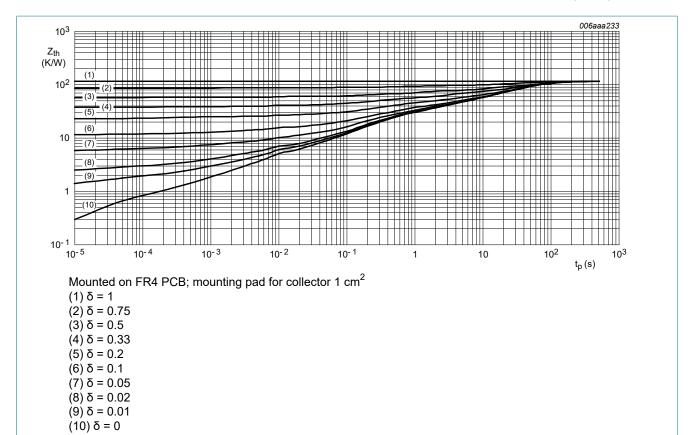
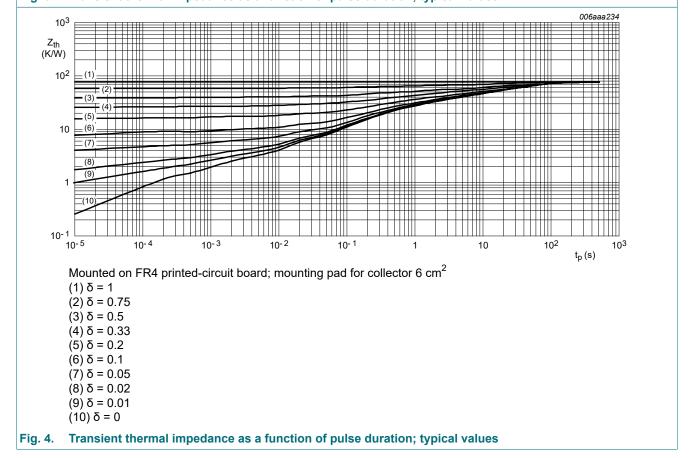


Fig. 3. Transient thermal impedance as a function of pulse duration; typical values



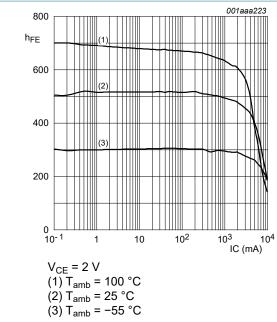
40 V, 5 A NPN low VCEsat (BISS) transistor

10. Characteristics

Table 7. Characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|--------------------|---|--|-----|-----|-----|------|
| СВО | collector-base cut-off | V _{CB} = 30 V; I _E = 0 A; T _{amb} = 25 °C | - | - | 100 | nA |
| | current | V _{CB} = 30 V; I _E = 0 A; T _j = 150 °C | - | - | 50 | μΑ |
| CES | collector-emitter cut-off current | $V_{CE} = 30 \text{ V}; V_{BE} = 0 \text{ V}; T_{amb} = 25 \text{ °C}$ | - | - | 100 | nA |
| ЕВО | emitter-base cut-off current | V _{EB} = 5 V; I _C = 0 A; T _{amb} = 25 °C | - | - | 100 | nA |
| η _E | DC current gain | V _{CE} = 2 V; I _C = 0.5 A; T _{amb} = 25 °C | 300 | - | - | |
| | | V_{CE} = 2 V; I_{C} = 1 A; $t_{p} \le 300 \ \mu s$; pulsed; $\delta \le 0.02$; T_{amb} = 25 °C | 300 | - | - | |
| | | V_{CE} = 2 V; I_{C} = 2 A; $t_{p} \le 300 \ \mu s$; pulsed; $\delta \le 0.02$; T_{amb} = 25 °C | 250 | - | - | |
| | | V_{CE} = 2 V; I_{C} = 5 A; $t_{p} \le 300 \ \mu s$; pulsed; $\delta \le 0.02$; T_{amb} = 25 °C | 100 | - | - | |
| V _{CEsat} | collector-emitter saturation voltage | I _C = 0.5 A; I _B = 5 mA; T _{amb} = 25 °C | - | - | 90 | mV |
| | | I _C = 1 A; I _B = 10 mA; T _{amb} = 25 °C | - | - | 120 | mV |
| | | I_C = 2 A; I_B = 200 mA; $t_p \le 300$ μs; pulsed; $\delta \le 0.02$; T_{amb} = 25 °C | - | - | 150 | mV |
| | | I_C = 4 A; I_B = 200 mA; $t_p \le 300$ μs; pulsed; $\delta \le 0.02$; T_{amb} = 25 °C | - | - | 290 | mV |
| | | $I_C = 5 \text{ A}; I_B = 500 \text{ mA}; t_p \le 300 \text{ µs};$ | - | - | 355 | mV |
| R _{CEsat} | collector-emitter saturation resistance | pulsed; δ ≤ 0.02; T _{amb} = 25 °C | - | 40 | 71 | mΩ |
| V _{BEsat} | base-emitter saturation voltage | I_C = 4 A; I_B = 200 mA; $t_p \le 300$ μs; pulsed; $\delta \le 0.02$; T_{amb} = 25 °C | - | - | 1.1 | V |
| | | I_C = 5 A; I_B = 500 mA; $t_p \le 300$ μs; pulsed; $\delta \le 0.02$; T_{amb} = 25 °C | - | - | 1.2 | V |
| V_{BEon} | base-emitter turn-on voltage | V_{CE} = 2 V; I_{C} = 2 A; $t_{p} \le 300 \ \mu s$; pulsed; $\delta \le 0.02$; T_{amb} = 25 °C | - | - | 1.1 | V |
| fт | transition frequency | $V_{CE} = 10 \text{ V}; I_{C} = 0.1 \text{ A}; f = 100 \text{ MHz};$ $T_{amb} = 25 \text{ °C}$ | 70 | - | - | MHz |
| C _c | collector capacitance | V_{CB} = 10 V; I_{E} = 0 A; i_{e} = 0 A; f = 1 MHz; T_{amb} = 25 °C | - | - | 75 | pF |

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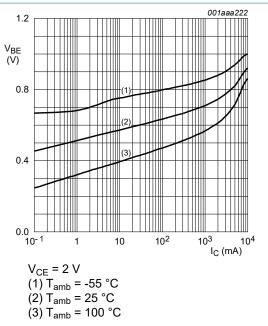


$$(1) T_{amb} = 100 °($$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig. 5. DC current gain as a function of collector current; typical values



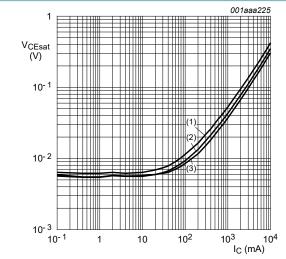
$$V_{CF} = 2 V$$

$$(1) T_{amb} = -55 °($$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

$$(3) T_{amb} = 100 °C$$

Fig. 6. Base-emitter voltage as a function of collector current; typical values



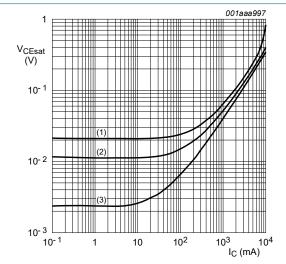
$$I_{\rm C}/I_{\rm B}=20$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

$$(3) T_{amb} = -55 °C$$

Fig. 7. Collector-emitter saturation voltage as a function of collector current; typical values



(1)
$$I_C/I_B = 100$$

(2)
$$I_C/I_B = 50$$

(3)
$$I_C/I_B = 10$$

Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values

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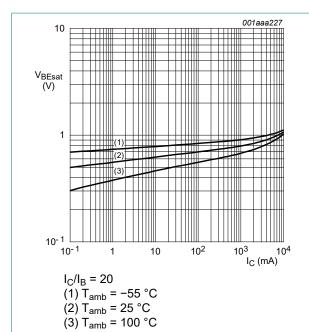
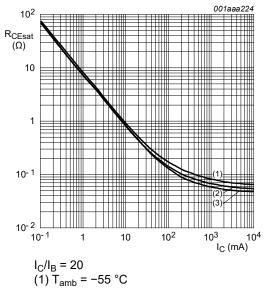
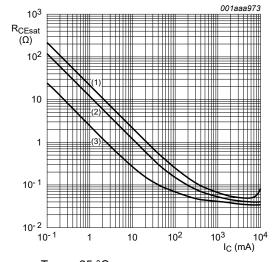


Fig. 9. collector current; typical values



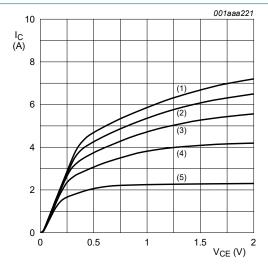
(1) $T_{amb} = -55 \,^{\circ}C$ (2) $T_{amb} = 25 \,^{\circ}C$ (3) $T_{amb} = 100 \,^{\circ}C$

Base-emitter saturation voltage as a function of Fig. 10. Equivalent on-resistance as a function of collector current; typical values



T_{amb} = 25 °C (1) $I_C/I_B = 100$ (2) $I_C/I_B = 50$ (3) $I_{\rm C}/I_{\rm B} = 10$

Fig. 11. Equivalent on-resistance as a function of collector current; typical values



(1) $I_B = 25 \text{ mA}$ (2) $I_B = 20 \text{ mA}$ (3) $I_B = 15 \text{ mA}$

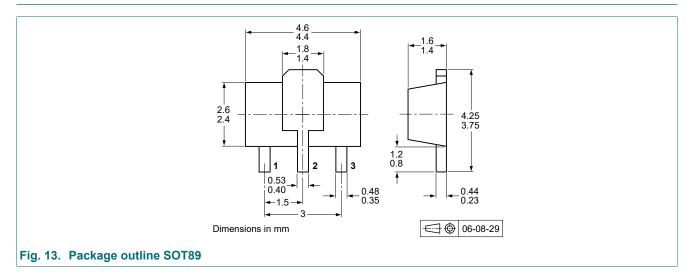
(4) $I_B = 10 \text{ mA}$

(5) $I_B = 5 \text{ mA}$

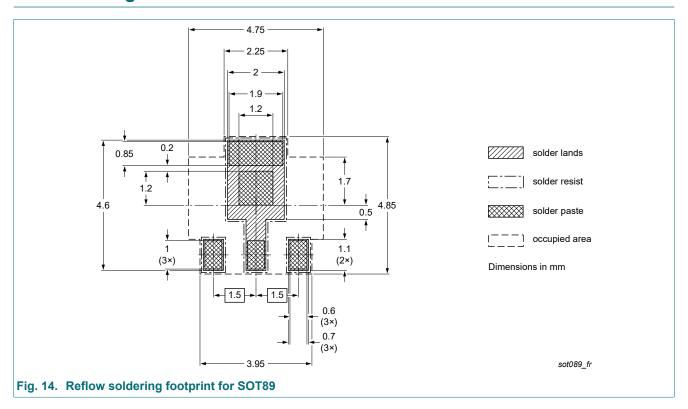
Fig. 12. Collector current as a function of collectoremitter voltage; typical values

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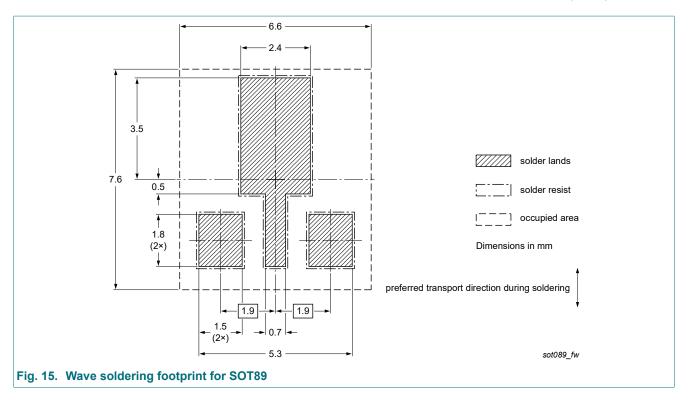
11. Package outline



12. Soldering



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13. Revision history

Table 8. Revision history

| Table 6. Revision in | Jotol y | | | |
|----------------------|--|--|--------------------|---------------|
| Data sheet ID | Release date | Data sheet status | Change notice | Supersedes |
| PBSS4540X v.3 | 20200415 | Product data sheet | - | PBSS4540X v.2 |
| Modifications: | Nexperia. Legal texts have Limiting values | this data sheet has been rede we been adapted to the new of a at I _{CM} : conditions corrected at figure 6: legend corrected | company name where | , , |
| PBSS4540X v.2 | 20041104 | Product data sheet | - | PBSS4540X v.1 |
| PBSS4540X v.1 | 20040611 | Product data sheet | - | - |

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14. Legal information

Data sheet status

| Document status [1][2] | Product status [3] | Definition |
|--------------------------------|-----------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
| Product [short] data sheet | Production | This document contains the product specification. |

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